

UNISONIC TECHNOLOGIES CO., LTD

UTT40N08 Preliminary Power MOSFET

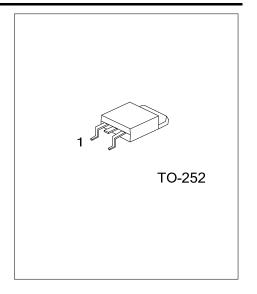
40A, 80V N-CHANNEL POWER MOSFET

■ DESCRIPTION

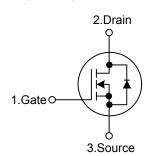
The **UTT40N08** power MOSFET provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness

■ FEATURES

- * $R_{DS(ON)}$ < $45m\Omega$ @ V_{GS} = 10 V
- * Low capacitance
- * Optimized gate charge
- * Fast switching capability
- * Avalanche energy specified



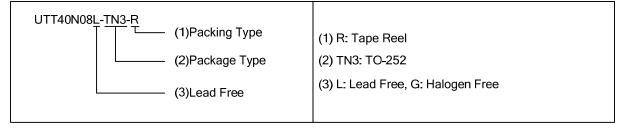
■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Doolsono	Pin Assignment			Daaldaa	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTT40N08L-TN3-R UTT40N08G-TN3-R		TO-252	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



■ MARKING INFORMATION

PACKAGE	MARKING			
TO-252	UTC UTT40N08 ☐ L: Lead Free G: Halogen Free Lot Code Data Code			

www.unisonic.com.tw 1 of 3

■ **ABSOLUTE MAXIMUM RATINGS** (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{ extsf{DSS}}$	80	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous	I _D	40	Α
	Pulsed (Note 1)	I_{DM}	160	Α
Power Dissipation	T _C =25°C	P _D	65	14/
	T _C =125°C		1.92	W
Junction Temperature		T_J	+150	Ŝ
Storage Temperature		T_{STG}	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	θ_{JA}	62	°C/W	
Junction to Case	θ _{JC}	1.92	°C/W	

■ ELECTRICAL CHARACTERISTICS (T_A =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	$I_D = 250 \mu A, V_{GS} = 0 V$	80			V		
Drain-Source Leakage Current	I _{DSS}	V _{DS} =80 V, V _{GS} =0 V, T _J =25°C			1	μΑ		
Gate- Source Leakage Current Forward	CCC	V _{GS} =+20V			+100	nA		
Reverse		V _{GS} =-20V			-100	nA		
ON CHARACTERISTICS								
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu A$	2.0		4.0	V		
Static Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =10V, I_D =20A		35	45	mΩ		
DYNAMIC PARAMETERS								
Input Capacitance	C _{ISS}			2800		pF		
Output Capacitance	Coss	V_{DS} =25 V, V_{GS} =0V, f=1.0MHz		320		pF		
Reverse Transfer Capacitance	C _{RSS}			140		pF		
SWITCHING PARAMETERS								
Total Gate Charge	Q_G			200		nC		
Gate to Source Charge	Q_{GS}	V_{DS} =25V, V_{GS} =10 V, I_{D} =40A		19		nC		
Gate to Drain Charge	Q_{GD}			14		nC		
Turn-ON Delay Time	t _{D(ON)}			66	78	ns		
Rise Time	t _R	V_{DS} =30 V, I_{D} =1 A, V_{GS} =10V,		52	70	ns		
Turn-OFF Delay Time	t _{D(OFF)}	$R_G = 1.7 \Omega$		350	380	ns		
Fall-Time	t _F			90	110	ns		
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Maximum Body-Diode Continuous Current	I _S	$V_D = V_G = 0V$, $V_S = 1.3V$			40	Α		
Maximum Body-Diode Pulsed Current	I _{SM}				160	Α		
Drain-Source Diode Forward Voltage	V_{SD}	T _J =25°C, I _S =40A, V _{GS} =0V			1.3	V		

Notes: 1. Pulse width limited by T_{J(MAX)}

2. Pulse width ≤300us, duty cycle ≤2%.

Power MOSFET

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

